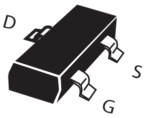
A1 N-Channel Enhancement Mode MOSFET ASM3400

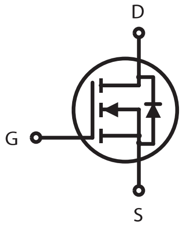
PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Max
30V	3.5A	50 @ V_{GS} = 10V 70 @ V_{GS} =4.5V

FEATURES

- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- SOT-23 package.

SOT-23





ABSOLUTE MAXIMUM RATINGS (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous [a] @ T_J=25 °C	I_D	3.5	A
-Pulsed [b]	I_{DM}	13	A
Drain-Source Diode Forward Current [a]	I_S	1.25	A
Maximum Power Dissipation [a]	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient [a]	R_{thJA}	100	°C/W